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74AHC1G66; 74AHCT1G66

Single-pole single-throw analog switch Rev. 04 — 18 December 2008

Product data sheet

General description 1.

74AHC1G66 and 74AHCT1G66 are high-speed Si-gate CMOS devices. They are single-pole single-throw analog switches. The switch has two input/output pins (Y and Z) and an active HIGH enable input pin (E). When pin E is LOW, the analog switch is turned

2. **Features**

- Very low ON resistance:
 - 26 Ω (typ.) at V_{CC} = 3.0 V
 - 16 Ω (typ.) at V_{CC} = 4.5 V
 - ◆ 14 Ω (typ.) at V_{CC} = 5.5 V
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - ♦ HMB JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101C exceeds 1000 V
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

Ordering information 3.

Table 1. **Ordering information**

Type number	Package								
	Temperature range	Name	Description	Version					
74AHC1G66GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package;	SOT353-1					
74AHCT1G66GW			5 leads; body width 1.25 mm						
74AHC1G66GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753					
74AHCT1G66GV									

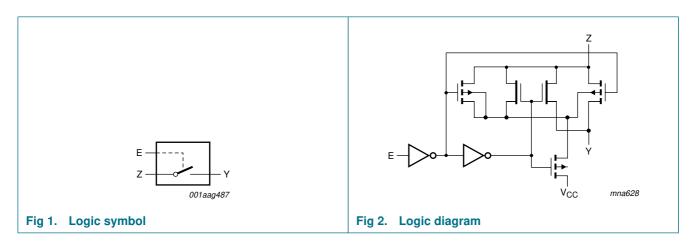


4. Marking

Table 2. Marking codes

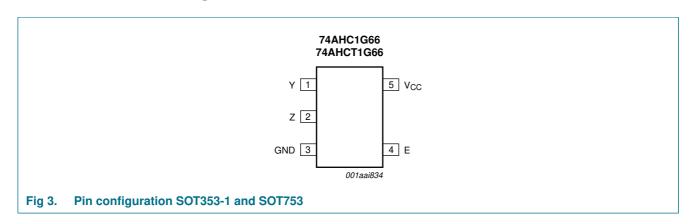
Type number	Marking
74AHC1G66GW	AL
74AHCT1G66GW	CL
74AHC1G66GV	A66
74AHCT1G66GV	C66

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
Υ	1	independent input or output
Z	2	independent input or output
GND	3	ground (0 V)
E	4	enable input (active HIGH)
V _{CC}	5	supply voltage

7. Functional description

Table 4. Function table[1]

Input E	Switch
L	OFF
Н	ON

^[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_1 < -0.5 V$	<u>[1]</u> –20	-	mA
I _{SK}	switch clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> _	±20	mA
I _{SW}	switch current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	75	mA
I_{GND}	ground current		–75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	250	mW

^[1] The input and output voltage ratings may be exceeded if the input and output voltage ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).[1]

Symbol	Parameter	Conditions	74AHC1G66			74AHCT1G66			Unit
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
V_{SW}	switch voltage		0	-	V_{CC}	0	-	V_{CC}	V

^[2] For TSSOP5 and SC-74A packages: above 87.5 °C the value of Ptot derates linearly with 4.0 mW/K.

Table 6. Recommended operating conditions ...continued

Voltages are referenced to GND (ground = 0 V).[1]

Symbol	Parameter	Conditions		74	74AHC1G66			74AHCT1G66		
				Min	Тур	Max	Min	Тур	Max	
T_{amb}	ambient temperature	'	·	-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and	$V_{CC}=3.3\pm0.3~V$	[2]	-	-	100	-	-	-	ns/V
	fall rate	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	[2]	-	-	20	-	-	20	ns/V

^[1] To avoid drawing V_{CC} current out of pin Z, when switch current flows in pin Y, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into pin Z, no V_{CC} current will flow out of terminal Y. In this case there is no limit for the voltage drop across the switch, but the voltage at pins Y and Z may not exceed V_{CC} or GND.

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

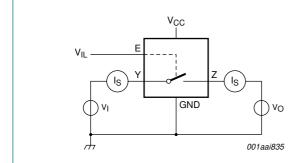
Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHC1	G66		'							
V_{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	٧
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	٧
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	٧
V_{IL}	LOW-level	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	٧
	input voltage	V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	٧
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	٧
I _I	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μΑ
I _{S(OFF)}	OFF-state leakage current	Y or Z; $V_{CC} = 5.5 \text{ V}$; see Figure 4	-	-	0.1	-	1.0	-	4.0	μΑ
I _{S(ON)}	ON-state leakage current	Y or Z; $V_{CC} = 5.5 \text{ V}$; see Figure 5	-	-	0.1	-	1.0	-	4.0	μΑ
I _{CC}	supply current	E, Y or Z = V_{CC} or GND; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	μΑ
C _I	input capacitance	E input	-	2.0	10	-	10	-	10	pF
C _{S(ON)}	ON-state capacitance	Y or Z input or output	-	4.0	10	-	10	-	10	pF
74AHCT	1G66									
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	8.0	-	0.8	-	0.8	V
I _I	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μΑ

^[2] Applies to control signal levels.

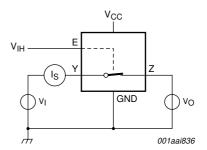
Table 7. Static characteristics ...continued Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C 1	to +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
I _{S(OFF)}	OFF-state leakage current	Y or Z; $V_{CC} = 5.5 \text{ V}$; see Figure 4	-	-	0.1	-	1.0	-	4.0	μΑ
I _{S(ON)}	ON-state leakage current	Y or Z; $V_{CC} = 5.5 \text{ V}$; see Figure 5	-	-	0.1	-	1.0	-	4.0	μΑ
I _{CC}	supply current	E, Y or Z = V_{CC} or GND; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	μΑ
ΔI_{CC}	additional supply current	per input pin; $V_I = 3.4 \text{ V}$; other inputs at V_{CC} or GND; $I_O = 0 \text{ A}$; $V_{CC} = 5.5 \text{ V}$	-	-	1.35	-	1.5	-	1.5	mA
Cı	input capacitance	E input	-	2.0	10	-	10	-	10	pF
C _{S(ON)}	ON-state capacitance	Y or Z input or output	-	4.0	10	-	10	-	10	pF

10.1 Test circuits



 $V_I = V_{CC} \mbox{ or GND and } V_O = \mbox{GND or } V_{CC}.$ Fig 4. Test circuit for measuring OFF-state leakage current



 $V_I = V_{CC}$ or GND and $V_O =$ open circuit.

Fig 5. Test circuit for measuring ON-state leakage current

10.2 ON resistance

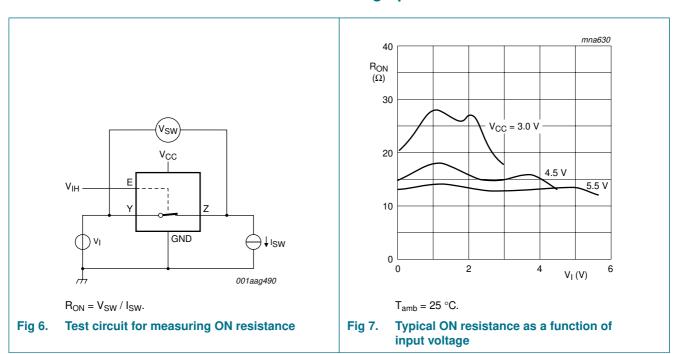
Table 8. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graph see Figure 7 11.

Symbol	Parameter	Conditions	25	°C	–40 °C to +85 °C	-40 °C to +125 °C	Unit
			Тур	max	Max	Max	
74AHC10	666 and 74AHC1	1G66					
R _{ON(peak)}		$V_I = V_{CC}$ to GND; see Figure 6					
	(peak)	$I_{SW} = 1.0 \text{ mA}; V_{CC} = 2.0 \text{ V}$	148 <mark>[1]</mark>	-	-	-	Ω
		$I_{SW} = 10 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$ to 3.6 V	28	50	70	110	Ω
		I_{SW} = 10 mA; V_{CC} = 4.5 V to 5.5 V	15	30	40	60	Ω
R _{ON(rail)}	ON resistance (rail)	V _I = GND; see <u>Figure 6</u>					
		$I_{SW} = 1.0 \text{ mA}; V_{CC} = 2.0 \text{ V}$	30	-	-	-	Ω
		$I_{SW} = 10 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$ to 3.6 V	20	50	65	90	Ω
		$I_{SW} = 10 \text{ mA}$; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	15	22	26	40	Ω
		V _I = V _{CC} ; see <u>Figure 6</u>					
		$I_{SW} = 1.0 \text{ mA}; V_{CC} = 2.0 \text{ V}$	28	-	-	-	Ω
		I_{SW} = 10 mA; V_{CC} = 3.0 V to 3.6 V	18	50	65	90	Ω
		$I_{SW} = 10 \text{ mA}; V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	13	22	26	40	Ω

^[1] At supply voltages approaching 2 V, the analog switch ON resistance becomes extremely non-linear. Therefore it is recommended that these devices be used to transmit digital signals only, when using this supply voltage.

10.3 ON resistance test circuit and graphs



11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF; unless otherwise specified; For test circuit see Figure 10.

Symbol	Parameter	Conditions		25	°C	-40 °C to +85 °C	-40 °C to +125 °C	Unit
				Typ[1]	max	Max	Max	
74AHC1	G66			'		'		
t _{pd}	propagation	Y to Z or Z to Y; see Figure 8	[2]					
	delay	$V_{CC} = 2.0 \text{ V}$		2.2	5.0	6.0	7.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.0	2.0	3.0	4.0	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.6	1.0	2.0	3.0	ns
t _{en}	enable time	E to Y or Z; see Figure 9	[2]					
		$V_{CC} = 2.0 \text{ V}; C_L = 15 \text{ pF}$		7.0	25.0	33.0	40.0	ns
		$V_{CC} = 2.0 \text{ V}$		11.0	35.0	46.0	57.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V};$ $C_L = 15 \text{ pF}$		4.0	11.0	14.0	18.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		5.8	15.0	20.0	25.0	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $C_L = 15 \text{ pF}$		3.0	8.0	10.0	13.0	ns
		V _{CC} = 4.5 V to 5.5 V		4.0	11.0	13.0	17.0	ns
t _{dis}	disable time	E to Y or Z; see Figure 9	[2]					
		$V_{CC} = 2.0 \text{ V}; C_L = 15 \text{ pF}$		9.0	25.0	33.0	40.0	ns
		V _{CC} = 2.0 V		13.0	35.0	46.0	57.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V};$ $C_L = 15 \text{ pF}$		6.0	11.0	14.0	18.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		8.4	15.0	20.0	25.0	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $C_L = 15 \text{ pF}$		5.0	8.0	10.0	13.0	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		6.1	11.0	13.0	17.0	ns
C_PD	power dissipation capacitance	$V_I = GND$ to V_{CC}	[3]	13	-	-	-	pF
74AHCT	1G66							
t _{pd}	propagation	Y to Z or Z to Y; see Figure 8	[2]					
	delay	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.7	1.0	2.0	3.0	ns
t _{en}	enable time	E to Y or Z; see Figure 9	[2]					
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $C_L = 15 \text{ pF}$		3.0	7.0	10.0	13.0	ns
		V _{CC} = 4.5 V to 5.5 V		4.7	10.0	13.0	17.0	ns
t _{dis}	disable time	E to Y or Z; see Figure 9	[2]					
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $C_L = 15 \text{ pF}$		5.0	8.0	10.0	13.0	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		6.5	11.0	13.0	17.0	ns

Table 9. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF; unless otherwise specified; For test circuit see Figure 10.

Symbol	Parameter	Conditions	25 °C		–40 °C to +85 °C	–40 °C to +125 °C	Unit
			Typ[1]	max	Max	Max	
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC}$ [3]	15	-	-	-	pF

- [1] All typical values are measured at V_{CC} = 2.0 V, V_{CC} = 3.3 V, V_{CC} = 5.0 V and T_{amb} = 25 °C.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .

 t_{en} is the same as t_{PZL} and t_{PZH} .

 t_{dis} is the same as t_{PLZ} and t_{PHZ} .

[3] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i + \Sigma \; ((C_L \times C_{SW}) \times V_{CC}{}^2 \times f_o) \; where:$$

 f_i = input frequency in MHz;

fo = output frequency in MHz;

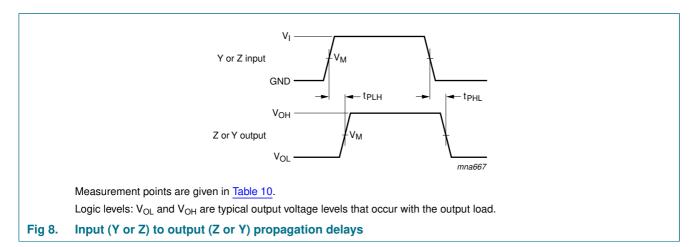
C_L = output load capacitance in pF;

C_{SW} = maximum switch capacitance in pF (see Table 7);

V_{CC} = supply voltage in Volt;

 $\Sigma \; ((C_L \times C_{SW}) \times V_{CC}{}^2 \times f_o) = sum \; of \; outputs.$

11.1 Waveforms and test circuit



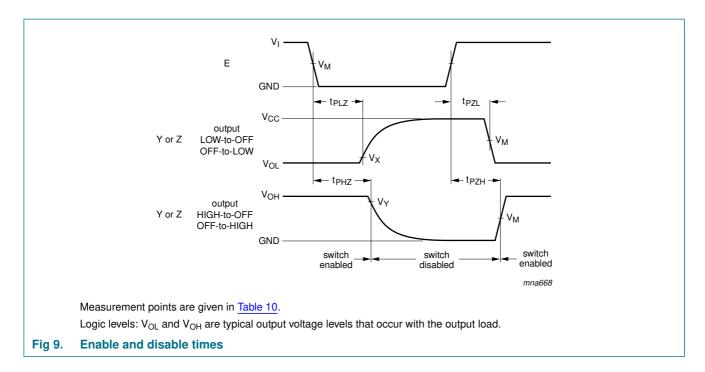
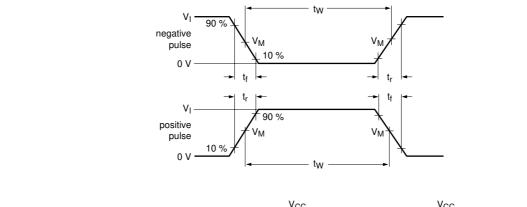
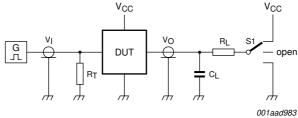


Table 10. Measurement points

Туре	Input	Output				
	V _M	V _M	V _X	V _Y		
74AHC1G66	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.3 V	V _{OH} – 0.3 V		
74AHCT1G66	1.5 V	1.5 V	V _{OL} + 0.3 V	V _{OH} – 0.3 V		





Test data is given in Table 11.

Definitions for test circuit:

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_I = Load resistance.

S1 = Test selection switch.

Fig 10. Test circuit for measuring switching times

Table 11. Test data

Туре	Input		Load		S1 position				
	VI	t _r , t _f	CL	RL	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}		
74AHC1G66	GND to V _{CC}	3 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}		
74AHCT1G66	GND to 3 V	3 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}		

11.2 Additional dynamic characteristics

Table 12. Additional dynamic characteristics for 74AHC1G66 and 74AHCT1G66 $GND = 0 \ V; \ t_r = t_f = 3.0 \ ns; \ C_L = 50 \ pF; \ unless \ otherwise \ specified.$ All typical values are measured at $T_{amb} = 25 \ ^{\circ}C$.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
THD total harmonic distortion	$f_i = 1 \text{ kHz}$; $R_L = 10 \text{ k}\Omega$; see Figure 11					
	V _{CC} = 3.0 V to 3.6 V	-	0.025	-	%	
	V _{CC} = 4.5 V to 5.5 V	-	0.015	-	%	
	$f_i = 10 \text{ kHz}$; $R_L = 10 \text{ k}\Omega$; see Figure 11					
	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}; V_{I} = 2.5 \text{ V}$	-	0.025	-	%	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}; V_I = 4.0 \text{ V}$	-	0.015	-	%

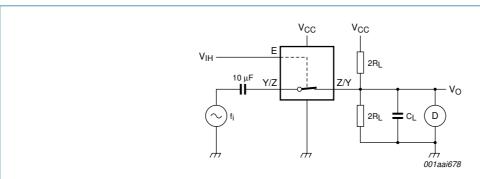
 Table 12.
 Additional dynamic characteristics for 74AHC1G66 and 74AHCT1G66 ...continued

GND = 0 V; $t_r = t_f = 3.0$ ns; $C_L = 50$ pF; unless otherwise specified. All typical values are measured at $T_{amb} = 25$ °C.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$f_{(-3dB)}$	–3 dB frequency response	$R_L = 50 \Omega$; $C_L = 10 pF$; see Figure 12 and 13				
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	230	-	MHz
		V _{CC} = 4.5 V to 5.5 V	-	280	-	MHz
$lpha_{iso}$	isolation (OFF-state)	$R_L = 600 \Omega$; $f_i = 1 MHz$; see Figure 14	[1]			
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}; V_I = 2.5 \text{ V}$	-	-50	-	dB
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}; V_I = 4.0 \text{ V}$	-	-50	-	dB

^[1] Adjust input voltage V_1 to 0 dBm level (0 dBm =1 mW into 50 Ω).

11.3 Test circuits and graphs

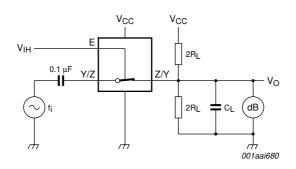


Test conditions:

 $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V; } V_I = 2.5 \text{ V (p-p)}.$

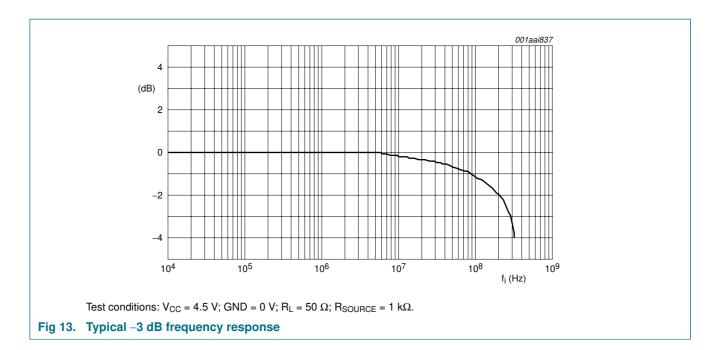
 $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V; } V_{I} = 4.0 \text{ V (p-p)}.$

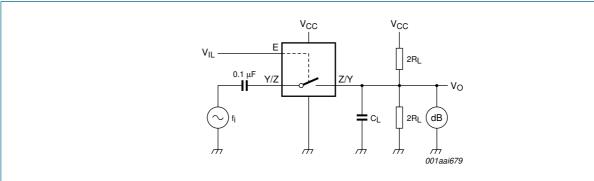
Fig 11. Test circuit for measuring total harmonic distortion



With $f_i = 1$ MHz adjust the switch input voltage for a 0 dBm level at the switch output, (0 dBm = 1 mW into 50 Ω). Then increase the input f_i frequency until the dB meter reads -3 dB.

Fig 12. Test circuit for measuring the -3 dB frequency response





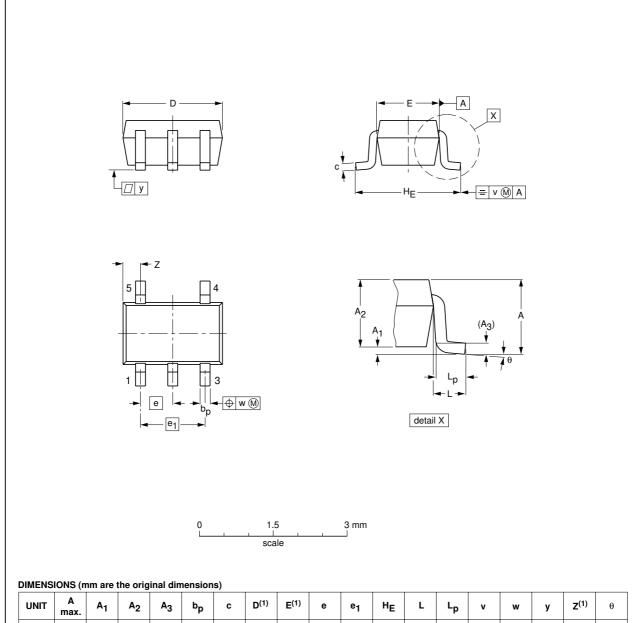
Adjust the switch input voltage for a 0 dBm level (0 dBm = 1 mW into 600 Ω).

Fig 14. Test circuit for measuring isolation (OFF-state)

12. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	C	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	HE	L	Lp	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	IOOUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT353-1		MO-203	SC-88A			-00-09-01 03-02-19	

Fig 15. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

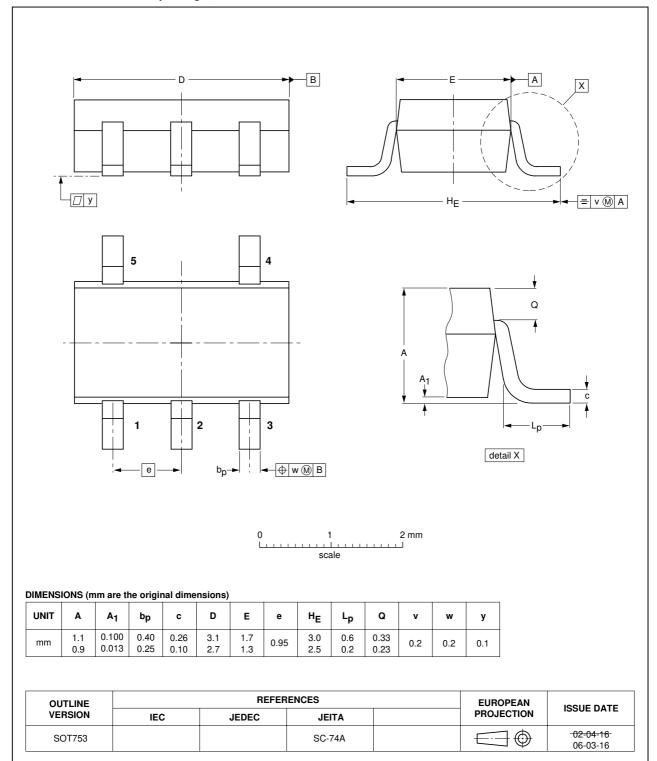


Fig 16. Package outline SOT753 (SC-74A)

13. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

14. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT1G66_4	20081218	Product data sheet	-	74AHC_AHCT1G66_3
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	with the new identity
	 Legal texts 	have been adapted to the ne	ew company name whe	ere appropriate.
	 Package S0 	OT353 changed to SOT353-	1 in <u>Table 1</u> and <u>Figure</u>	<u>15</u> .
	 Quick Refer 	rence Data and Soldering se	ections removed.	
	Section 2 "F	eatures" updated.		
74AHC_AHCT1G66_3	20020606	Product specification	-	74AHC_AHCT1G66_2
74AHC_AHCT1G66_2	20020215	Product specification	-	74AHC_AHCT1G66_1
74AHC_AHCT1G66_1	20010129	Product specification	-	-

74AHC1G66; 74AHCT1G66

Single-pole single-throw analog switch

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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74AHC1G66; 74AHCT1G66

NXP Semiconductors

Single-pole single-throw analog switch

17. Contents

1	General description
2	Features
3	Ordering information 1
4	Marking 2
5	Functional diagram 2
6	Pinning information 2
6.1	Pinning
6.2	Pin description
7	Functional description 3
8	Limiting values
9	Recommended operating conditions 3
10	Static characteristics 4
10.1	Test circuits 5
10.2	ON resistance
10.3	ON resistance test circuit and graphs 6
11	Dynamic characteristics 7
11.1	Waveforms and test circuit 8
11.2	Additional dynamic characteristics 10
11.3	Test circuits and graphs
12	Package outline
13	Abbreviations
14	Revision history
15	Legal information
15.1	Data sheet status
15.2	Definitions
15.3	Disclaimers
15.4	Trademarks16
16	Contact information 16
17	Contents

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